

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

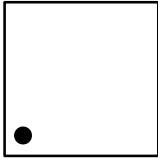
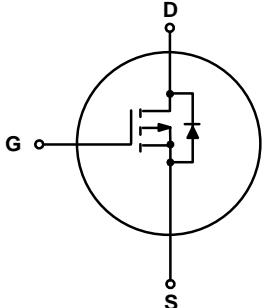
#### 1.2 Applications

- Motor drivers
- DC - DC Converter

#### 1.3 Quick reference

- $BV \geq 35\text{ V}$
- $R_{DS(ON)} \leq 3.6\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 41\text{ W}$
- $R_{DS(ON)} \leq 5.3\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- $I_D \leq 88\text{ A}$

### 2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View DFN3x3-8L	
4	Gate		
5,6,7,8	Drain		

## 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	Drain-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	35	-	V
$V_{GS}$	Gate-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	-	$\pm 20$	V
$I_D^{*,***}$	Drain Current	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	88	A
$I_{DM}^{*,**,***}$	Pulsed Source Current	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	144	A
$P_{tot}^*$	Total Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	-	41	W
$T_{stg}$	Storage Temperature		- 55	150	$^\circ\text{C}$
$T_J$	Junction Temperature		-	150	$^\circ\text{C}$
$I_S$	Diode Forward Current	$T_C = 25\text{ }^\circ\text{C}$	-	88	A
$R_{\theta JA}^*$	Thermal Resistance- Junction to Ambient		-	62.5	$^\circ\text{C} / \text{W}$
$R_{\theta JC}^*$	Thermal Resistance- Junction to Case		-	3	

Notes :

- \* Surface Mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$
- \*\* Pulse width  $\leq 10\text{ }\mu\text{s}$ , duty cycle  $\leq 1\%$
- \*\*\* Limited by bonding wire

## 4. Marking Information

Product Name	Marking
KJ02035QL	<div style="display: flex; align-items: center;"> <div style="background-color: black; color: white; padding: 5px; margin-right: 10px;"> <b>02035</b>  <b>YWWXXX</b> </div> <div> <b>YWWXXX:</b>  <b>Date Code</b> </div> </div>

## 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ02035QL	DFN3*3			5000	

Note: KUAJIEXIN defines " Green " as lead-free ( RoHS compliant ) and halogen free ( Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C )



**6. Electrical Characteristics** ( $T_A = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	35	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250\text{ }\mu\text{A}$	1.0	-	3.0	V
$I_{DSS}$	Zero Gate Voltage Source Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$T_J = 85\text{ }^\circ\text{C}$	-	-	30	$\mu\text{A}$
$I_{GSS}$	Gate Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA
$R_{DS(ON)}^a$	Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	-	2.8	3.6	m $\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	4.1	5.3	
<b>Diode Characteristics</b>						
$V_{SD}^a$	Diode Forward Voltage	$I_{SD} = 20\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 20\text{ A}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	36.8	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	32.4	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V}$ Frequency = 1 MHz	-	2652	-	pF
$C_{oss}$	Output Capacitance		-	887	-	
$C_{rss}$	Reverse Transfer Capacitance		-	96	-	
$t_d(on)$	Turn-on Delay Time	$V_{DS} = 15\text{ V}, V_{GEN} = 10\text{ V},$ $R_G = 4.5\text{ }\Omega, R_L = 0.75\text{ }\Omega,$ $I_{DS} = 20\text{ A}$	-	9.4	-	ns
$t_r$	Turn-on Rise Time		-	29.8	-	
$t_d(off)$	Turn-off Delay Time		-	39.4	-	
$t_f$	Turn-off Fall Time		-	18.6	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V},$ $I_{DS} = 20\text{ A}$	-	46.5	-	nC
$Q_{gs}$	Gate-Source Charge		-	10.1	-	
$Q_{gd}$	Gate-Drain Charge		-	8.8	-	

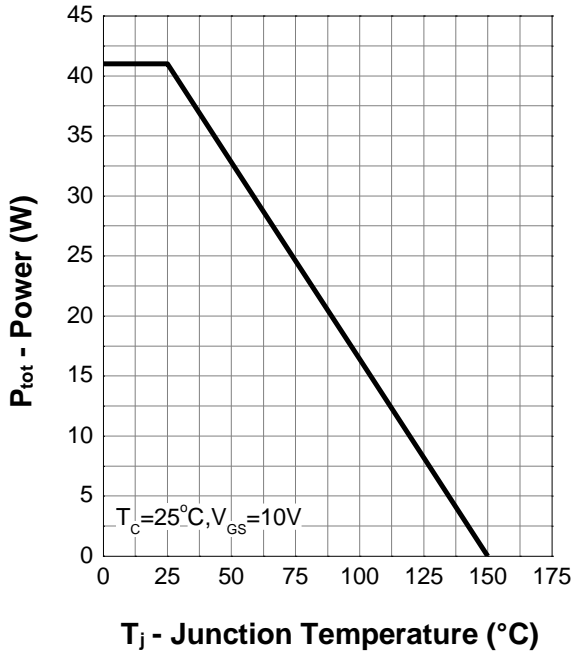
Notes :

- a : Pulse test ; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b : Guaranteed by design, not subject to production testing

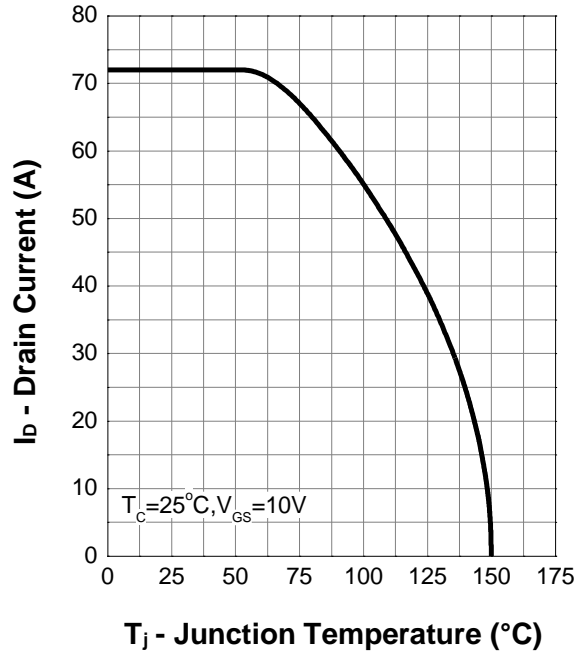


### 7. Typical Characteristics (Cont.)

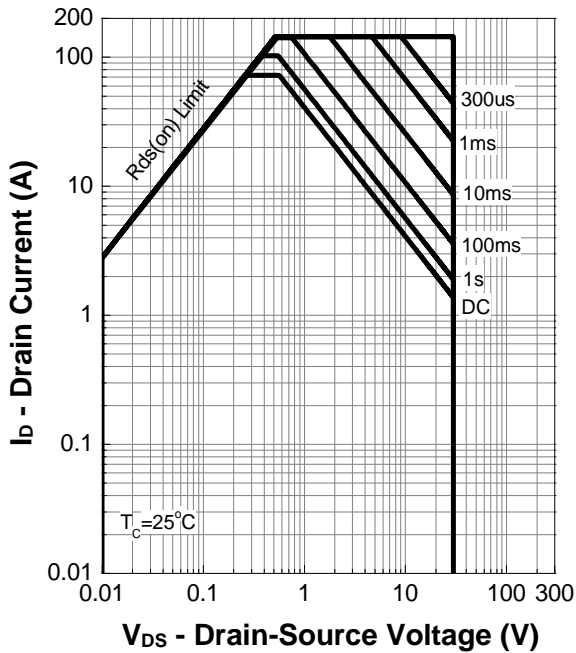
Power Capability



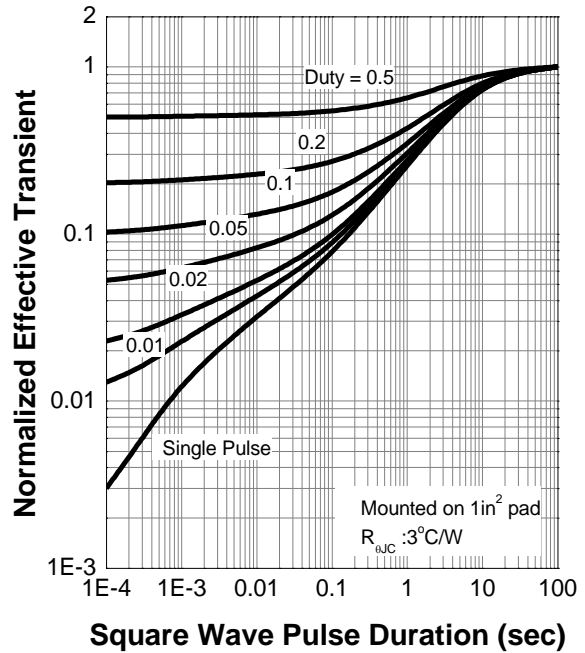
Current Capability



Safe Operating Area



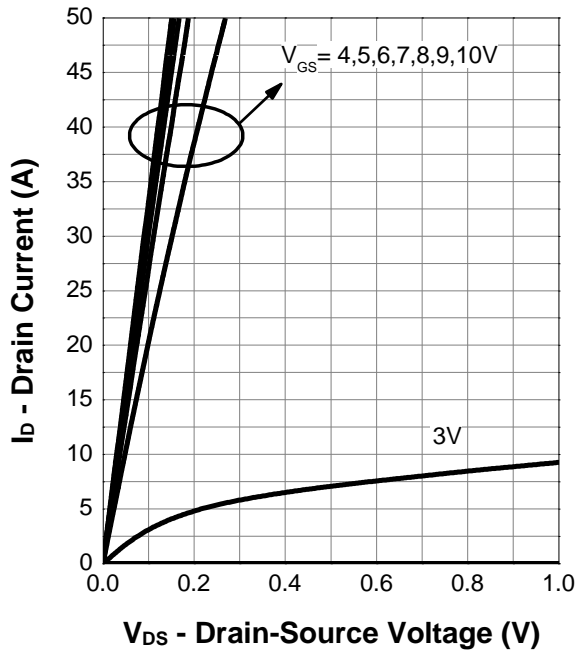
Transient Thermal Impedance



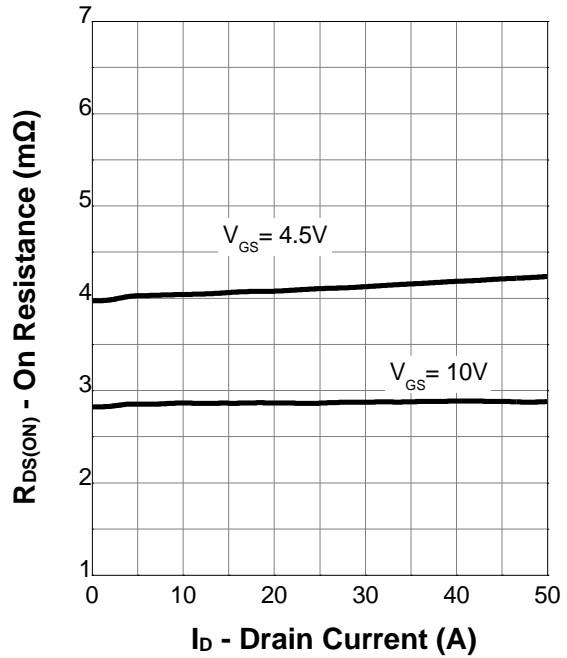


### 7. Typical Characteristics (Cont.)

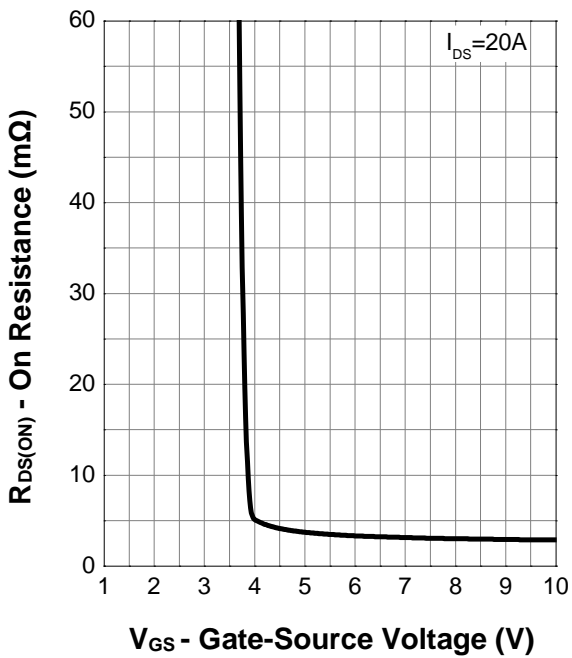
Output Characteristics



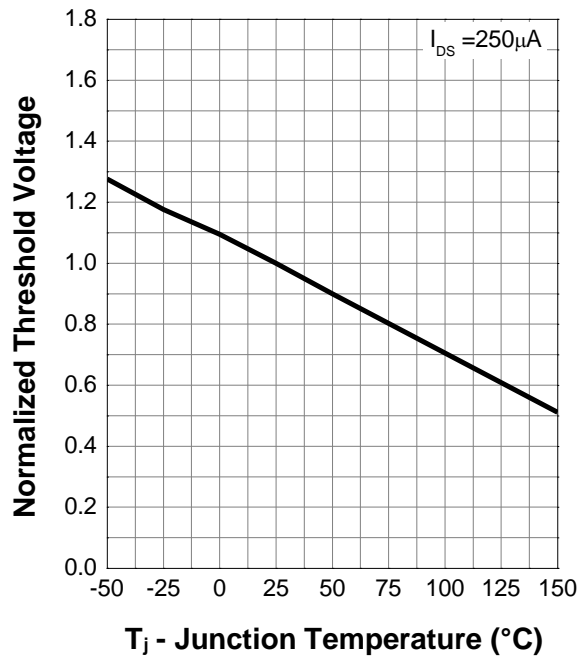
On Resistance



Transfer Characteristics

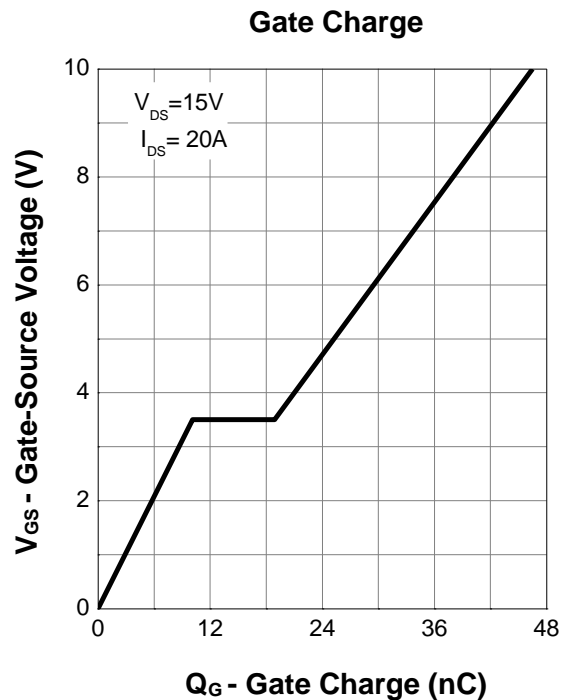
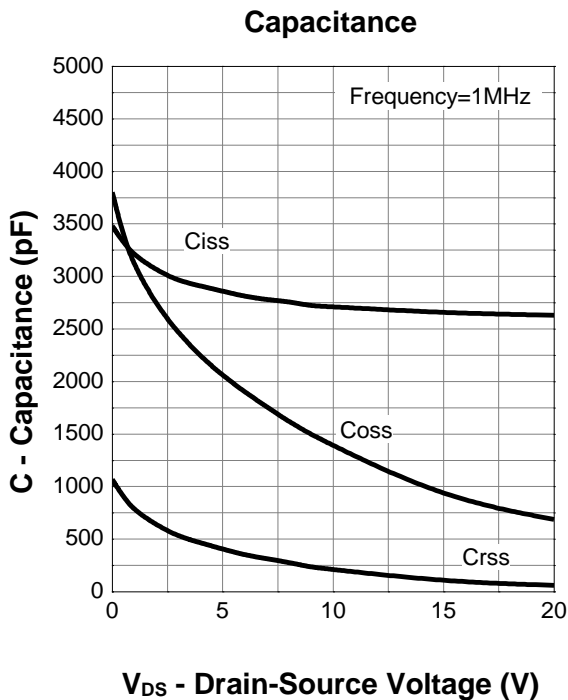
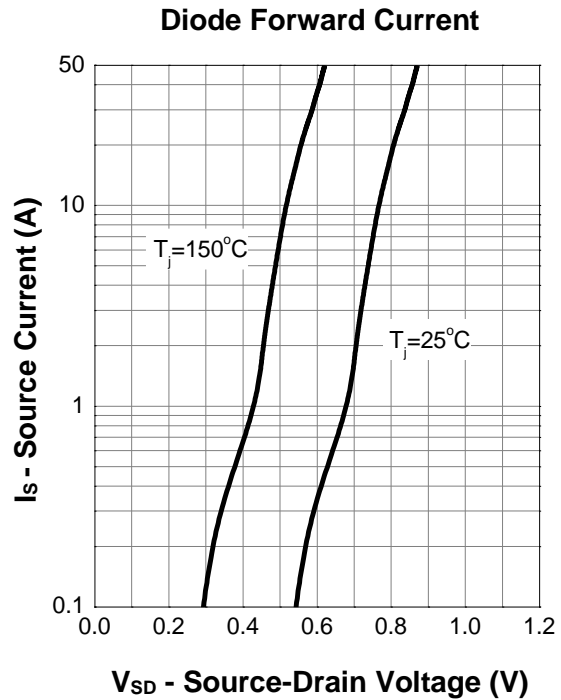
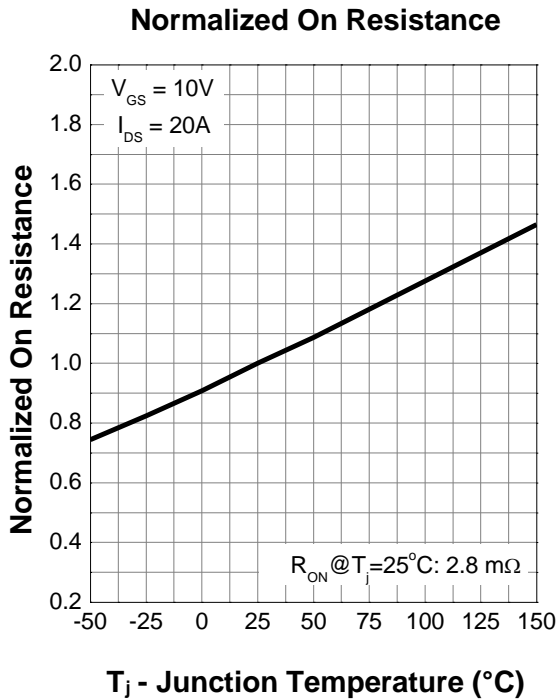


Normalized Threshold Voltage





### 7. Typical Characteristics (Cont.)



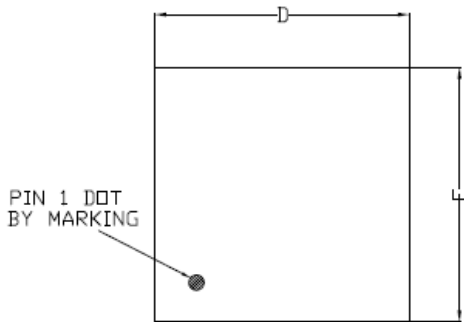


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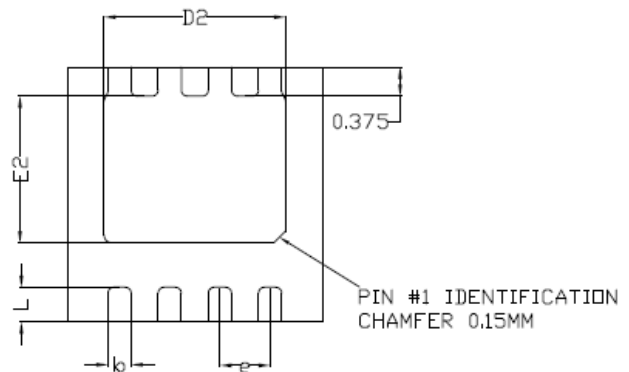
KJ02035QL

## 8. Package Dimensions

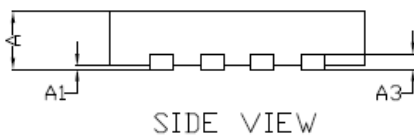
DFN3x3 - 8L Package



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Lead finish : NiPdAu

Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.7	0.8
A1	0.00	0.05
A3	0.20 REF	
D	3.25	3.35
E	3.25	3.35
D2	2.30	2.40
E2	1.85	1.95
b	0.25	0.35
L	0.35	0.55
e	0.65 BSC	